

c. Amendments to Claims

1 – 7. (Cancelled)

5 8. (Previously presented) A process for making a structure, comprising:
providing a solid body comprising MgB_2 ;
ejecting MgB_2 from the body by directing laser light onto the body; and
growing an MgB_2 layer on a surface of a substrate with a portion of the ejected
 MgB_2 .

10 9. (Original) The process of claim 8, wherein the substrate and MgB_2
have lattice constants along the surface that match to at least 10 percent.

10. (Original) The process of claim 8, further comprising forming the solid body
by sintering MgB_2 .

15 11. (Original) The process of claim 8, wherein the ejecting includes directing
light from a pulsed laser onto the body.

20 12. (Previously presented) The process of claim 8, wherein the substrate
comprises one of SiC , LaAlO_3 , SrTiO_3 , and sapphire.

25 13. (Original) The process of claim 8, wherein the ejecting and growing are
performed in a vacuum chamber that is maintained at a pressure of less than about 10^{-2}
Torr.

14. (Previously presented) The process of claim 8, wherein the ejecting and
growing are performed in a vacuum chamber that is maintained at a pressure of greater
than about 10^{-6} Torr.

30 15. (Original) The process of claim 13, wherein the growing produces a
crystalline or polycrystalline layer of MgB_2 whose thickness is at least 10 nm.

16. (Previously presented) The process of claim 8, wherein the solid body is a solid body of MgB_2 .

17. (Previously presented) The process of claim 8, wherein the MgB_2 layer is
5 grown from a portion of the ejected MgB_2 .

18. (Previously presented) The process of claim 17, wherein the solid body is a solid body of MgB_2 .

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